

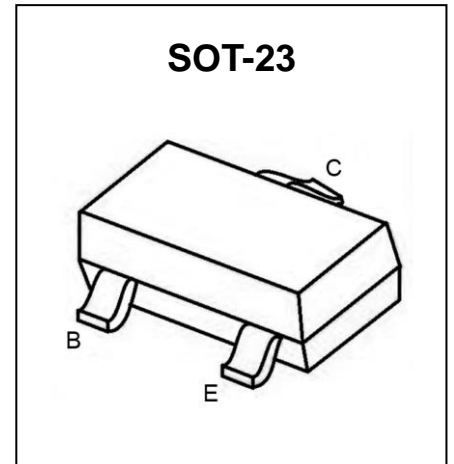
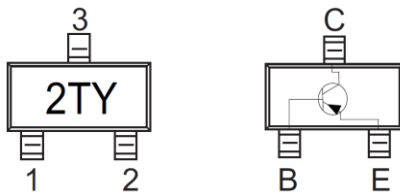


S8550 Transistor(PNP)

Featur

- Good current characters
- Small saturable voltage drop
- High Breakdown voltage

Marking:



Classification of h_{FE}:

Rank	L	H	J
Range	120-200	200-350	300-400

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

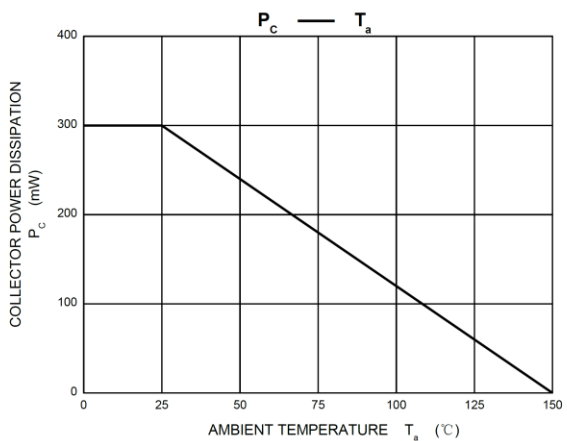
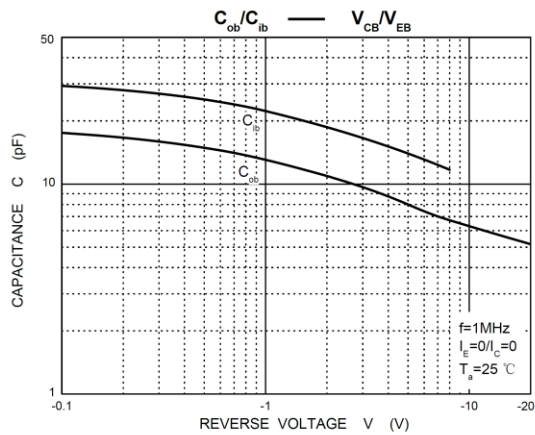
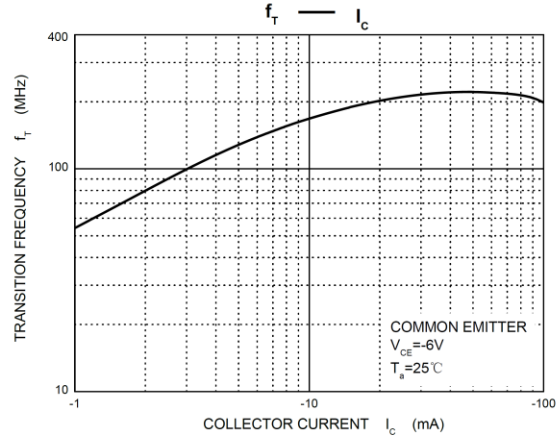
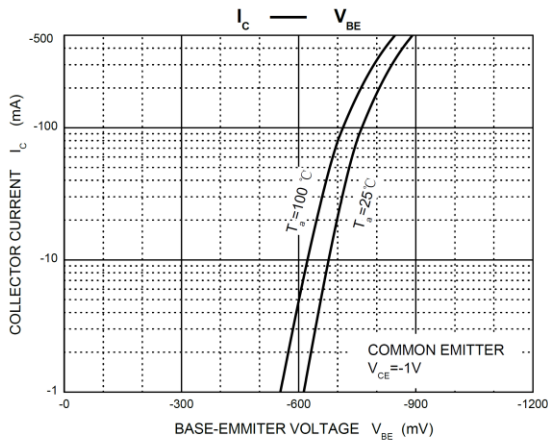
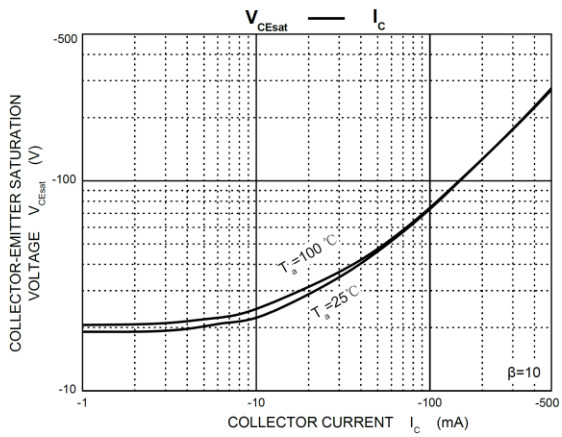
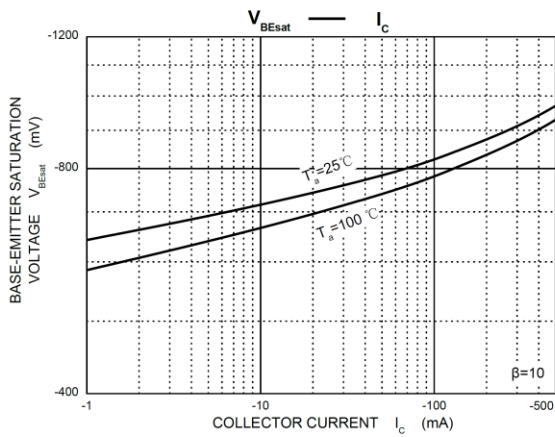
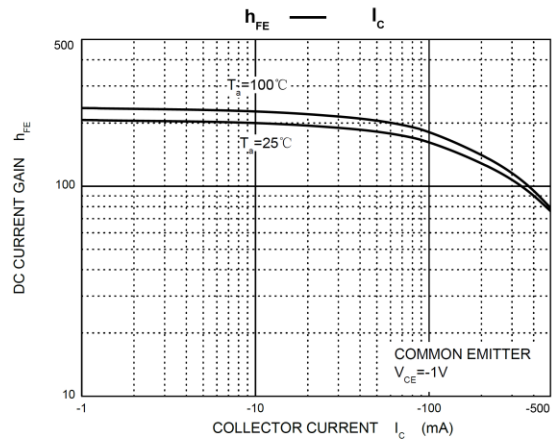
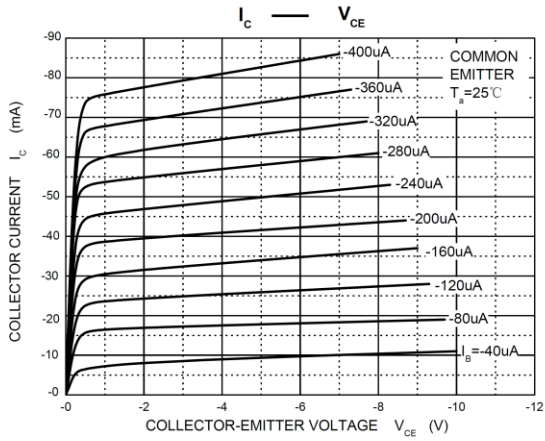
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CE0}	-25	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current -Continuous	I _c	-0.5	A
Power Dissipation	P _d	300	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

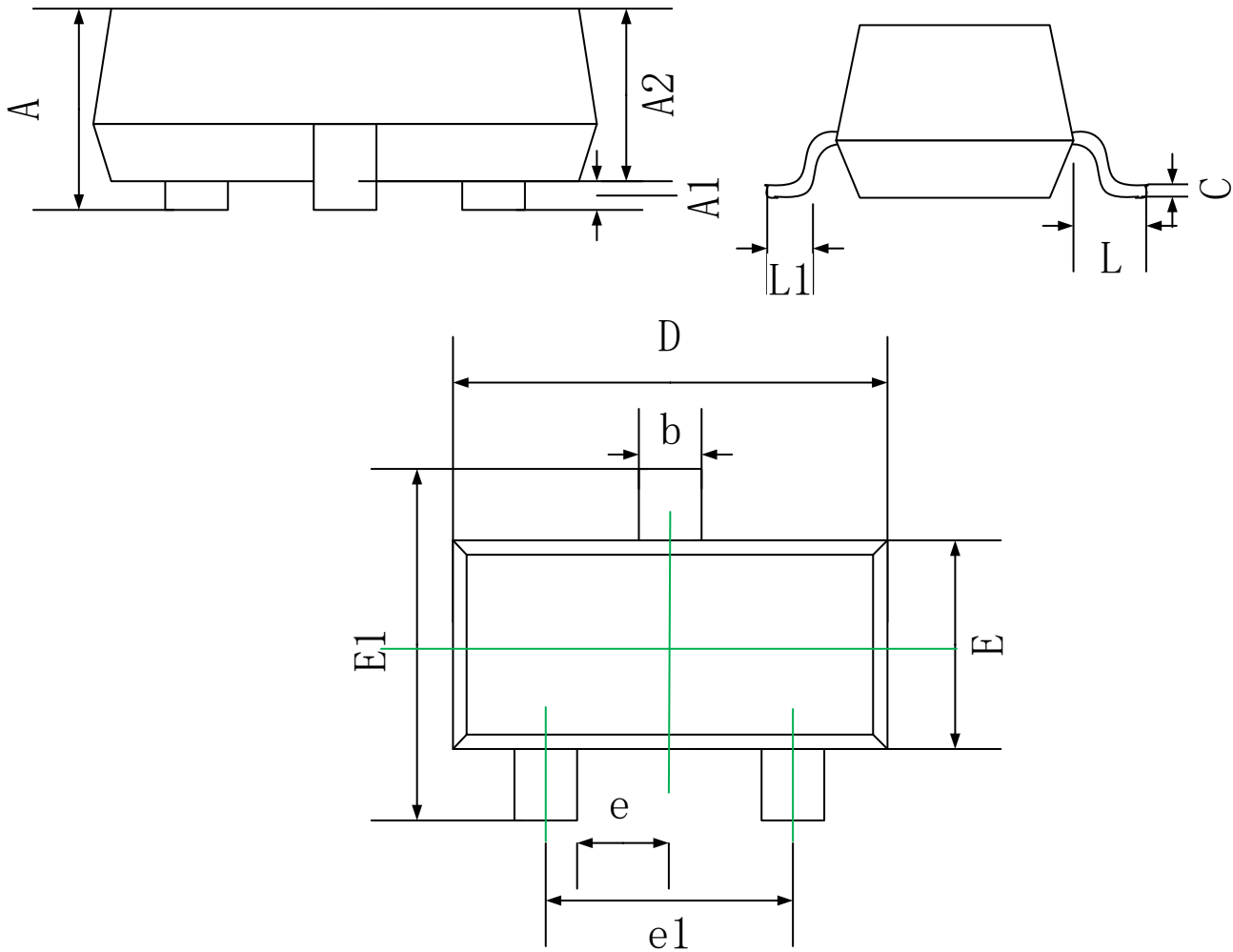
ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	V(BR) _{CBO}	I _C =-100μA, I _E =0	-40		V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C =-1mA, I _B =0	-25		V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E =-100μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0		-100	nA
Collector cut-off current	I _{CEO}	V _{CE} =-20V, I _B =0		-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0		-100	nA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-0.1mA	40		
		V _{CE} =-1V, I _C =-1mA	70		
		V _{CE} =-1V, I _C =-50mA	100	400	
		V _{CE} =-1V, I _C =-100mA	60		
		V _{CE} =-1V, I _C =-500mA	30		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA		-0.5	V
		I _C =-500mA, I _B =-50mA		-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA		-1.1	V
		I _C =-500mA, I _B =-50mA		-1.2	V
Transition frequency	f _T	V _{CE} = -6V, I _C =-10mA, f=30MHz	150		MHZ
Input Capacitance	C _{IB}	V _{CB} = -5V, I _E =0, f=1MHz		4.0	pF
Output Capacitance	C _{OB}	V _{EB} = -0.5V, I _C =0, f=1MHz		8.0	pF
Delay Time	t _d	V _{CC} =-3V, V _{BE} =0.5V, I _C =-10mA, I _B =-1.0mA		35	nS
Rise Time	t _r			35	nS
Storage Time	t _s	V _{CC} =-3V, V _{BE} =0.5V, I _{B1} =I _{B2} =-1.0mA		200	nS
Fall Time	t _f			50	nS

*Pulse Test : Pulse width<300Us , Duty Cycle < 2.0%.

Typical Characteristics



SOT-23 Package Information


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.15
A1	0.00	0.10
A2	0.90	1.05
b	0.30	0.50
c	0.08	0.15
D	2.80	3.00
E	1.20	1.40
E1	2.25	2.55
e	0.95 REF.	
e1	1.80	2.00
L	0.55 REF.	
L1	0.30	0.50

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)